

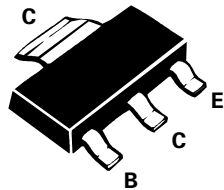
PNP SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

ISSUE 1 - JANUARY 1997

FZT1149A

FEATURES

- * $V_{CE0} = -25V$
- * 4 Amp Continuous Current
- * 10 Amp Pulse Current
- * Low Saturation voltage
- * High Gain



SOT223

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-10	A
Continuous Collector Current	I_C	-4	A
Base Current	I_B	-500	mA
Power Dissipation at $T_{amb}=25^{\circ}C$ †	P_{tot}	2.5	W
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

† The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 2 inches x 2 inches

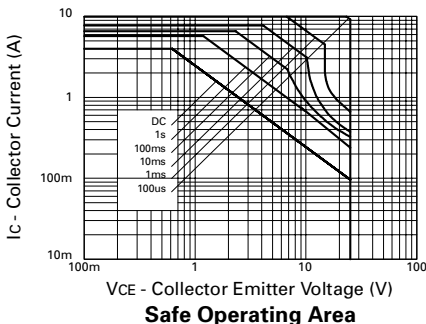
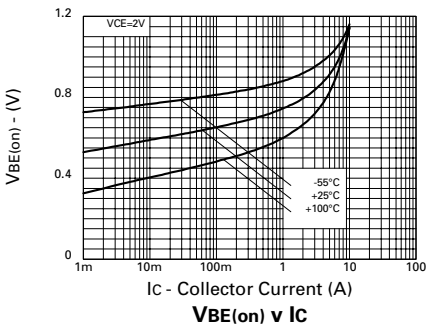
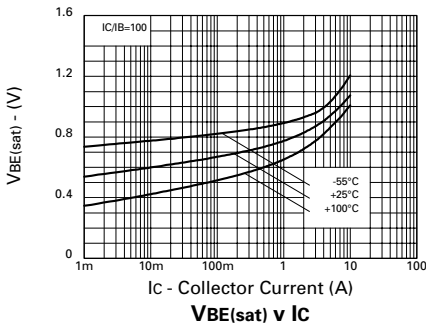
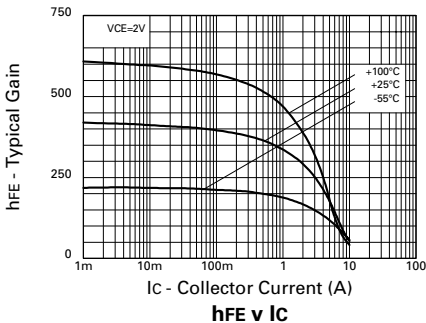
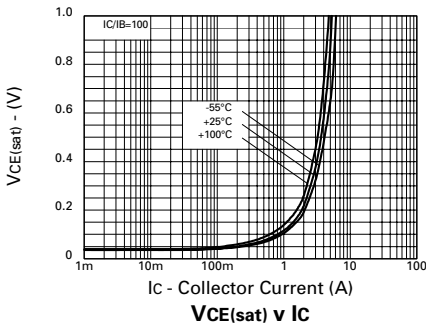
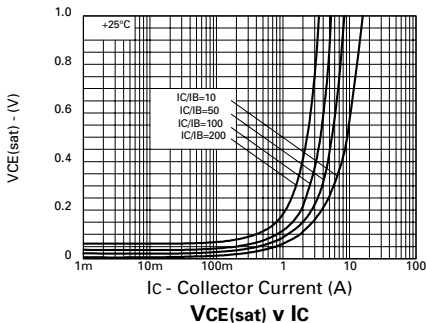
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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$).

PARAMETER	SYMBOL	VALUE			UNIT	CONDITIONS.
		MIN.	TYP.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-30	-70		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	V_{CES}	-25	-60		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	V_{CEO}	-25	-60		V	$I_C = -10\text{mA}$ *
Collector-Emitter Breakdown Voltage	V_{CEV}	-25	-60		V	$I_C = -100\mu\text{A}$, $V_{EB} = +1\text{V}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-8.5		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}		-0.3	-100	nA	$V_{CB} = -24\text{V}$
Emitter Cut-Off Current	I_{EBO}		-0.3	-100	nA	$V_{EB} = -4\text{V}$
Collector Emitter Cut-Off Current	I_{CES}		-0.3	-100	nA	$V_{CE} = -20\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-45 -100 -140 -170 -230	-80 -170 -240 -260 -350	mV mV mV mV mV	$I_C = -0.1\text{A}$, $I_B = -1.0\text{mA}$ * $I_C = -0.5\text{A}$, $I_B = -3\text{mA}$ * $I_C = -1\text{A}$, $I_B = -7\text{mA}$ * $I_C = -2\text{A}$, $I_B = -30\text{mA}$ * $I_C = -4\text{A}$, $I_B = -140\text{mA}$ *
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-960	-1050	mV	$I_C = -4\text{A}$, $I_B = -140\text{mA}$ *
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-860	-1000	mV	$I_C = -4\text{A}$, $V_{CE} = -2\text{V}$ *
Static Forward Current Transfer Ratio	h_{FE}	270 250 195 115	450 400 320 190 50	800		$I_C = -10\text{mA}$, $V_{CE} = -2\text{V}$ * $I_C = -0.5\text{A}$, $V_{CE} = -2\text{V}$ * $I_C = -2\text{A}$, $V_{CE} = -2\text{V}$ * $I_C = -5\text{A}$, $V_{CE} = -2\text{V}$ * $I_C = -10\text{A}$, $V_{CE} = -2\text{V}$ *
Transition Frequency	f_r		135		MHz	$I_C = -50\text{mA}$, $V_{CE} = -10\text{V}$ $f = 50\text{MHz}$
Output Capacitance	C_{cb}		50		pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$
Switching Times	t_{on}		150		ns	$I_C = -4\text{A}$, $I_B = -40\text{mA}$, $V_{CC} = -10\text{V}$
	t_{off}		270		ns	$I_C = -4\text{A}$, $I_B = \pm 40\text{mA}$, $V_{CC} = -10\text{V}$

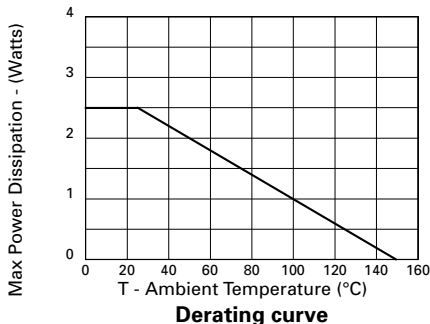
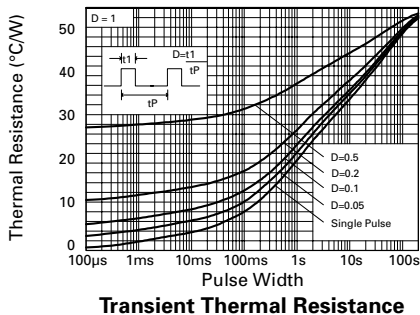
*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS



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THERMAL CHARACTERISTICS



SPICE PARAMETERS

*ZETEX FZT1149A Spice model Last revision 10/1/97

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+ RE=20e-3 RB=150e-3 RC=10e-3 CJE=490e-12
+ CJC=150e-12 VJC=1.094 MJC=0.4739 TF=1e-9 TR=3.5e-9
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